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					APPLICANT Klaus Florian Schuegraf et al.			
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U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA							
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
EO	AC	④	Ohnishi, K. et al., <i>Improving Gate Oxide Integrity (GOI) of a W/Wn/dual-poly Si Stacked-Gate by Using Wet-Hydrogen Oxidation in 0.14- μm CMOS Devices</i> , IEEE, 1998, pgs. 397-400.					
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